

# 2SC4562G

## Silicon NPN epitaxial planar type

For high-frequency amplification

Complementary to 2SA1748G

### ■ Features

- High transition frequency  $f_T$
- Small collector output capacitance (Common base, input open circuited)  $C_{ob}$
- S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

### ■ Package

- Code  
SMini3-F2
- Marking Symbol: AM
- Pin Name  
1: Base  
2: Emitter  
3: Collector

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	50	V
Collector-emitter voltage (Base open)	$V_{CEO}$	50	V
Emitter-base voltage (Collector open)	$V_{EBO}$	5	V
Collector current	$I_C$	50	mA
Collector power dissipation	$P_C$	150	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

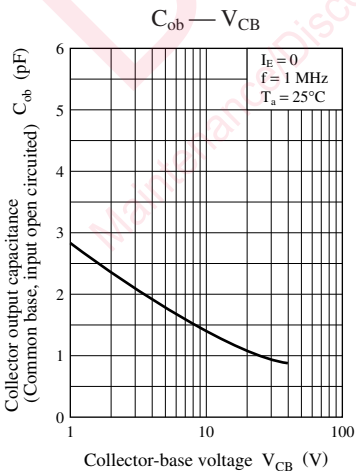
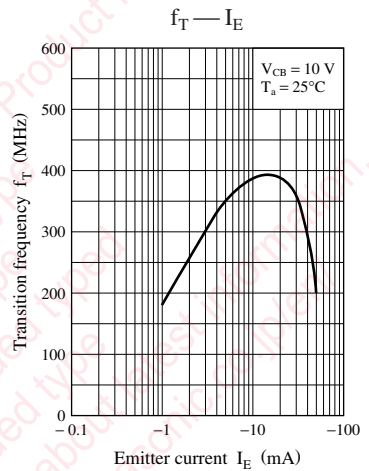
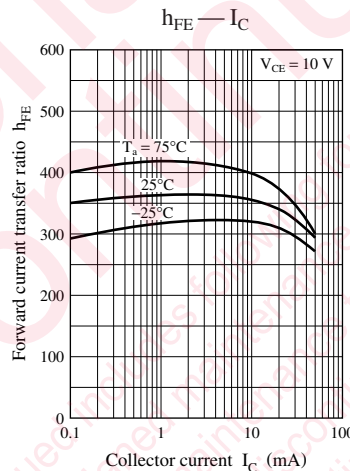
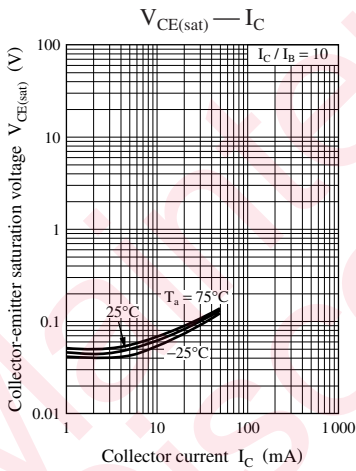
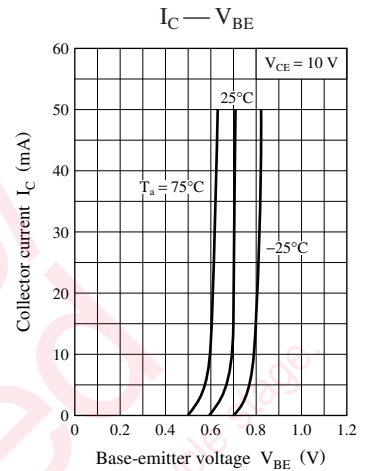
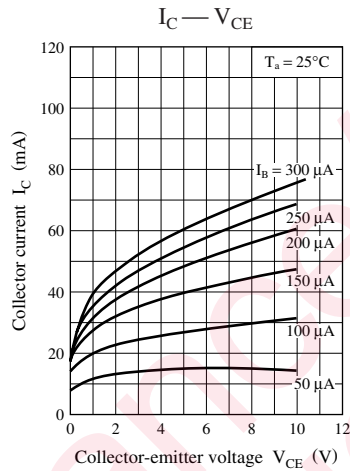
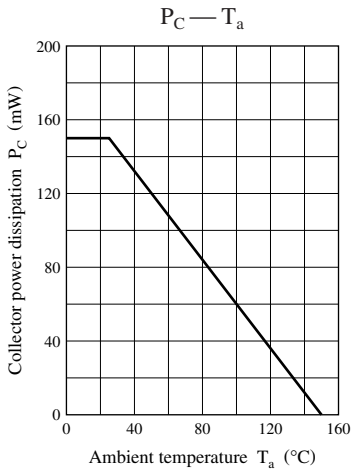
### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = 10 \mu\text{A}, I_E = 0$	50			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 1 \text{mA}, I_B = 0$	50			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = 10 \mu\text{A}, I_C = 0$	5			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 10 \text{V}, I_E = 0$			0.1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = 10 \text{V}, I_B = 0$			100	$\mu\text{A}$
Forward current transfer ratio *	$h_{FE}$	$V_{CE} = 10 \text{V}, I_C = 2 \text{mA}$	200		500	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10 \text{mA}, I_B = 1 \text{mA}$		0.06	0.30	V
Transition frequency	$f_T$	$V_{CB} = 10 \text{V}, I_E = -2 \text{mA}, f = 200 \text{MHz}$		250		MHz
Collector output capacitance (Common base, input open circuited)	$C_{ob}$	$V_{CB} = 10 \text{V}, I_E = 0, f = 1 \text{MHz}$		1.5		pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

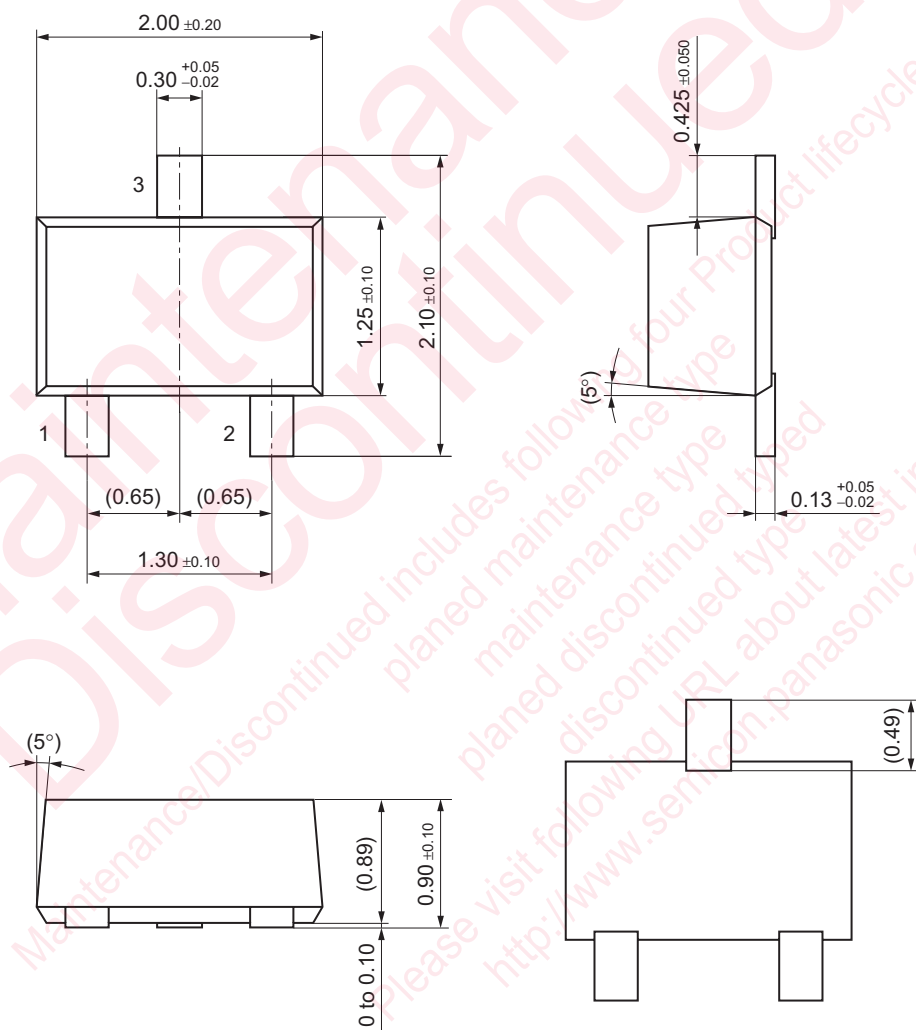
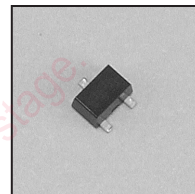
2. \*: Rank classification

Rank	Q	R
$h_{FE}$	200 to 400	250 to 500



SMini3-F2

Unit: mm



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